ASSP For Power Supply Applications (General Purpose DC/DC Converter)

2-Channel DC/DC Converter IC

with Overcurrent Protection Symmetrical-Phase Type

MB39A106

■ DESCRIPTION

The MB39A106 is a symmetrical-phase type of two-channel, DC/DC converter IC using pulse width modulation (PWM), incorporating an overcurrent protection circuit (requiring no current sense resistor) and an overvoltage protection circuit. Providing high output driving capabilities, the MB39A106 is suitable for down-conversion.

The MB39A106 adopts both synchronous rectification to provide high efficiency and symmetrical phasing (two anti-phase triangular waves) which contributes to making the input capacitor small.

The MB39A106 contains a Bootstrap diode resulting in a reduced number of components used. It also contains a variety of protection features which output the protection status upon detection of an overvoltage or overcurrent while reducing the number of external protective devices required.

The result is an ideal built-in power supply for driving products with high speed CPU's such as home TV game devices and notebook PC's.

■ FEATURES

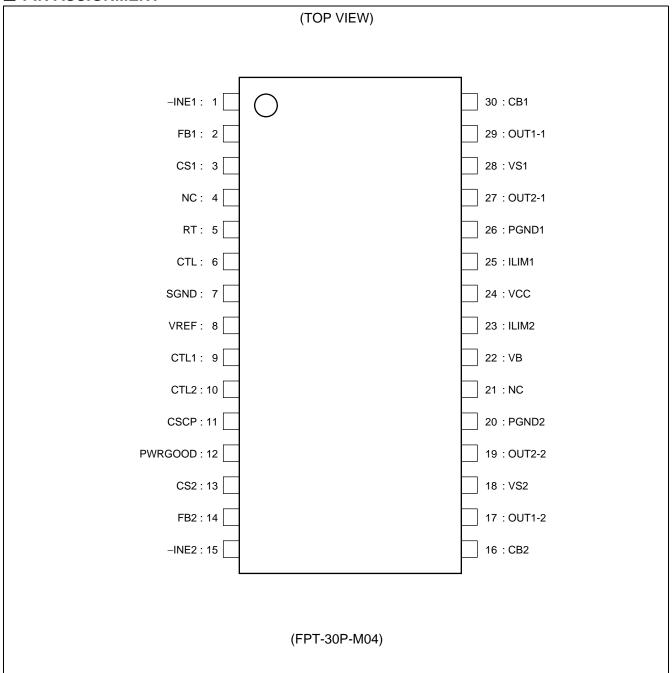
- Built-in bootstrap diode
- Built-in timer-latch overcurrent protection circuit (requiring no current sense resistor)
- Built-in timer-latch overvoltage protection circuit
- Synchronous rectification system providing high efficiency
- Power supply voltage range: 6.5 V to 18 V
- PWRGOOD terminals (open-drain) to output the protection status
- Symmetrical-phase system reducing the input capacitor loss
- Built-in channel control function
- One type of package (TSSOP-30pin : 1 type)
- Reference voltage: 3.5 V ± 1 %
- Error amplifier threshold voltage: 1.23 V \pm 1 % (Ta = 0 °C to + 85 °C)
- Support for frequency setting using an external resistor (Frequency setting capacitor integrated)
- Oscillation frequency range: 100 kHz to 500 kHz
- Standby current : 0 μA (Typ)
- Built-in circuit for load-independent soft-start and discharge control
- Built-in totem-pole output for N-ch MOS FET
- One type of package (TSSOP-30 pin : 1 type)

APPLICATION

- Home Video Game
- IP phone
- Printer etc.



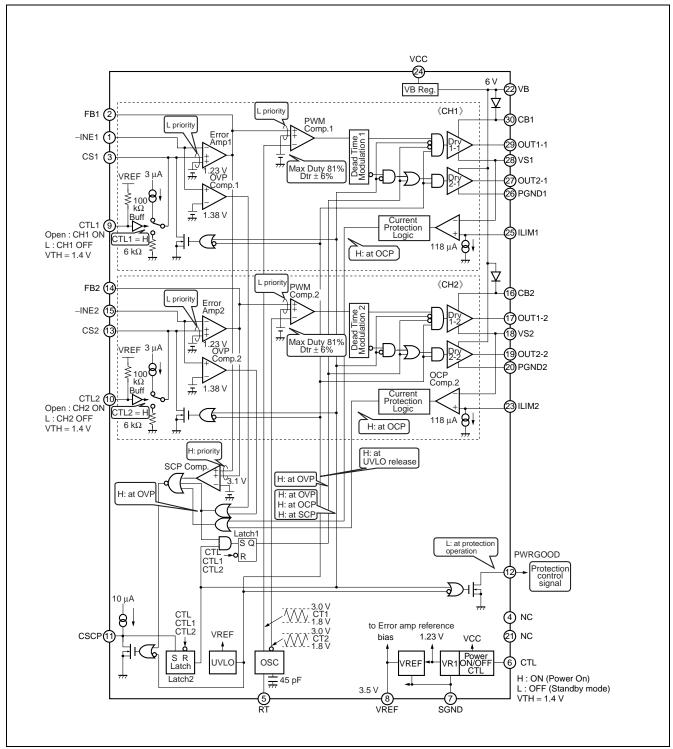
■ PIN ASSIGNMENT



■ PIN DESCRIPTION

Pin No.	Symbol	I/O	Descriptions		
1	-INE1	Į	CH1 error amp inverted input terminal		
2	FB1	0	CH1 error amp output terminal		
3	CS1	_	CH1 soft-start capacitor connection terminal		
4	NC	_	No connection		
5	RT	_	Triangular waveform oscillation frequency setting resistor connection terminal		
6	CTL	I	Power supply control terminal "H" level : IC operating mode "L" level : IC Standby mode		
7	SGND		Ground terminal		
8	VREF	0	Reference voltage output terminal		
9	CTL1	I	CH1 control terminal "H" level : CH1 ON state "L" level : CH1 OFF state and protection status reset		
10	CTL2	1	CH2 control terminal "H" level : CH2 ON state "L" level : CH2 OFF state and protection status reset		
11	CSCP	_	Timer-latch short-circuit protection capacitor connection terminal		
12	PWRGOOD	0	CH1, CH2 protection status output terminal		
13	CS2	_	CH2 soft-start capacitor connection terminal		
14	FB2	0	CH2 error amp output terminal		
15	-INE2	I	CH2 error amp inverted input terminal		
16	CB2	_	CH2 boot capacitor connection terminal Connect a capacitor between the CB2 and VS2 terminals.		
17	OUT1-2	0	CH2 totem-pole output terminal (External main-side FET gate drive)		
18	VS2	_	CH2 external main-side FET source connection terminal		
19	OUT2-2	0	CH2 totem-pole output terminal (External synchronous-rectification-side FET gate drive)		
20	PGND2		Ground terminal		
21	NC		No connection		
22	VB	0	Output circuit bias output terminal		
23	ILIM2	I	CH2 overcurrent detection resistor connection terminal		
24	VCC		Reference voltage, control circuit power supply terminal		
25	ILIM1	I	CH1 overcurrent detection resistor connection terminal		
26	PGND1	_	Ground terminal		
27	OUT2-1	0	CH1 totem-pole output terminal (External synchronous-rectification-side FET gate drive)		
28	VS1	_	CH1 external main-side FET source connection terminal		
29	OUT1-1	0	CH1 totem-pole output terminal (External main-side FET gate drive)		
30	CB1	_	CH1 boot capacitor connection terminal Connect a capacitor between the CB1 and VS1 terminals.		

■ BLOCK DIAGRAM



■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Condition	Rat	Unit	
Parameter	Syllibol	Condition	Min	Max	Onit
Power-supply voltage	Vcc	_	_	20	V
Boot voltage	Vсв	CB terminal	_	25	V
Output current	lo	_		120	mA
Peak output current	ЮР		_	800	mA
Power dissipation	P _D	Ta ≤ +25 °C	_	1390*	mW
Storage temperature	Тѕтс	_	-55	+125	°C

 $^{^{\}star}$: The packages are mounted on the dual-sided epoxy board (10 cm \times 10 cm) .

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Cymbal	Condition		Value	Value		
Parameter	Symbol	Condition	Min	Тур	Max	Unit	
Power-supply voltage	Vcc	_	6.5	12	18	V	
Boot voltage	Vсв	CB terminal	_	_	24	V	
Reference voltage output current	lor	VREF terminal	– 1		0	mA	
Bias output current	Іов	VB terminal	– 1	_	0	mA	
	VIN	-INE terminal	0	_	Vcc - 1.8	V	
Input voltage	Vctl	CTL1, CTL2 terminal	0	_	Vref	V	
	VCIL	CTL terminal	0	_	Vcc	V	
Output voltage	V _{PG}	PWRGOOD terminal	0	_	15	V	
Output current	lo	_	- 100	_	+100	mA	
Peak output current	ЮР		- 700		+700	mA	
Oscillation frequency	fosc	_	100	300	500	kHz	
Timing resistor	R⊤	_	30	47	130	kΩ	
Boot capacitor	Св	_	_	0.1	1.0	μF	
Reference voltage output capacitor	CREF	VREF terminal	_	0.1	1.0	μF	
Bias output capacitor	Сув	VB terminal	1.0	4.7	10	μF	
Soft-start capacitor	Cs	_	_	0.1	1	μF	
Short-circuit detection capacitor	CSCP	_	_	0.01	1	μF	
Overcurrent detection setting resistor	RLIM	_	0.1	1	10	kΩ	
Operating ambient temperature	Ta		- 30	+ 25	+ 85	°C	

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

> Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

> No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ ELECTRICAL CHARACTERISTICS

(VCC = 12 V, VB = 0 mA, VREF = 0 mA, Ta = +25 °C)

Parameter		Compleal	Pin	Canditions		Value		Unit
Parai	meter	Symbol	No.	Conditions	Min	Тур	Max	Unit
		V _{REF}	8	Ta = + 25 °C	3.465	3.500	3.535	V
Reference	Output voltage	ΔV _{REF} /	8	Ta = 0 °C to + 85 °C	_	0.5*	_	%
Voltage	Input stability	Line	8	VCC = 6.5 V to 18 V	_	1	10	mV
Block [REF]	Load stability	Load	8	VREF = 0 mA to - 1 mA	_	3	10	mV
	Short-circuit output current	los	8	VREF = 0 V	- 40	- 20	- 10	mA
Bias Voltage Block [VB]	Output voltage	Vв	22	_	5.88	6.00	6.12	V
Triangular Waveform	Oscillation frequency	fosc	17, 29	$R_T = 47 \text{ k}\Omega$	270	300	330	kHz
Oscillator Block [OSC]	Frequency/ temperature variation	Δfosc/ fosc	17, 29	Ta = 0 °C to + 85 °C	_	1*	_	%
Undervoltage	Threshold voltage	Vтн	8	VREF = _√	2.6	2.8	3.0	V
(VCC) Lockout Circuit Block [UVLO]	Hysteresis width	Vн	8	_	_	0.2*		V
Blook [8 v 2 0]	Reset voltage	Vrst	8	VREF = ₹	1.7	2.1	2.5	V
Short-circuit Protection	Threshold voltage	Vтн	11	_	0.65	0.70	0.75	V
Circuit Block [SCP]	Input source current	Icscp	11	_	– 14	- 10	-6	μА
Overcurrent Protection	ILIM terminal input current	Іым	23, 25	$R_T = 47 \text{ k}\Omega$	106	118	130	μА
Circuit Block [OCP]	Offset voltage	Vio	23, 25	_	_	1*	_	mV
Overvoltage Protection	Threshold voltage	Vтн	1, 15	-INE = _√	1.35	1.38	1.41	V
Circuit Block [OVP]	Input bias current	Ів	1, 15	-INE = 0 V	-730	-110	_	nA
Protection Status Output Circuit Block [PWRGOOD]	Output leakage current	ILEAK	12	PWRGOOD = 5 V	_	_	40	μА
	Output "L" level voltage	Vol	12	PWRGOOD = 1 mA	_	0.1	0.4	V
Soft-start Circuit Block [CS]	Charge current	Ics	3, 13	_	- 4.2	- 3.0	- 1.8	μА

(VCC = 12 V, VB = 0 mA, VREF = 0 mA, Ta = +25 °C)

Parameter			Pin		-	Value		1111
Para	meter	Symbol	No.	Conditions	Min	Тур	Max	Unit
	Threshold	V _{TH1}	1, 15	FB = 2.4 V, Ta = + 25 °C	1.221	1.230	1.239	V
	voltage	V _{TH2}	1, 15	FB = 2.4 V, $Ta = 0 ^{\circ}\text{C to} + 85 ^{\circ}\text{C}$	1.218	1.230	1.242	V
	Input bias current	lв	1, 15	-INE = 0 V	- 730	- 110		nA
Error Amp	Voltage gain	A∨	2, 14	DC	60	100		dB
Block [Error Amp]	Frequency bandwidth	BW	2, 14	$A_V = 0 dB$		1.5*		MHz
	Output voltage	V _{FBH}	2, 14	_	3.2	3.4		V
	Output voltage	V _{FBL}	2, 14	_		40	200	mV
	Output source current	Isource	2, 14	FB = 2.4 V		-2	– 1	mA
	Output sink current	İsink	2, 14	FB = 2.4 V	150	250	_	μА
•	Threshold	VTL	2, 14	Duty cycle = 0 %	1.7	1.8	1	V
	voltage	Vтн	2, 14	Duty cycle = Dtr	_	2.86	3.00	V
Dead Time Control Block [DTC]	Maximum duty cycle	Dtr	17, 29	$R_T = 47 \text{ k}\Omega$	75	81	87	%
	Output current (main side)	Isource1	17, 29	OUT1 = 12 V, CB = 17 V, VS = 12 V, Duty \leq 5 % (t = 1/ fosc × Duty)	_	- 700*	_	mA
		İsink1	17, 29	OUT1 = 17 V, CB = 17 V, VS = 12 V, Duty \leq 5 % (t = 1/ fosc × Duty)	_	900*		mA
Output Block [Drive]	Output voltage	Vон1	17, 29	OUT1 = - 100 mA, CB = 17 V, VS = 12 V	V _{СВ} - 2.5	V _{CB} - 0.9	_	V
	(main side)	V _{OL1}	17, 29	OUT1 = 100 mA, CB = 17 V, VS = 12 V	_	Vs + 0.9	Vs + 1.4	V
	Output current (synchronous	Isource2	19, 27	OUT2 = 0 V, Duty \leq 5 % (t = 1/ fosc × Duty)		- 7 50*		mA
	rectification side)	Isink2	19, 27	OUT2 = 6 V, Duty \leq 5 % (t = 1/ fosc × Duty)	—	900*	_	mA

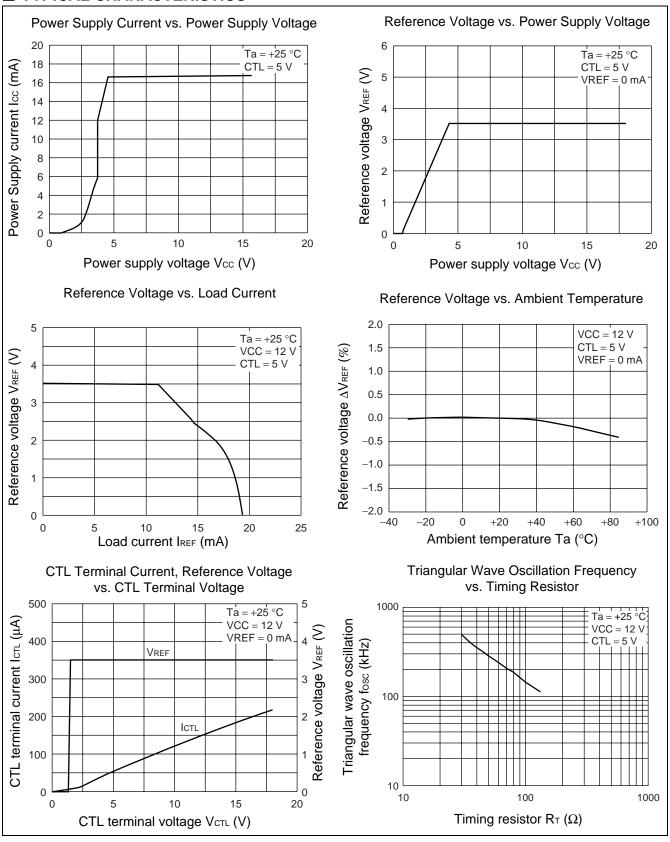
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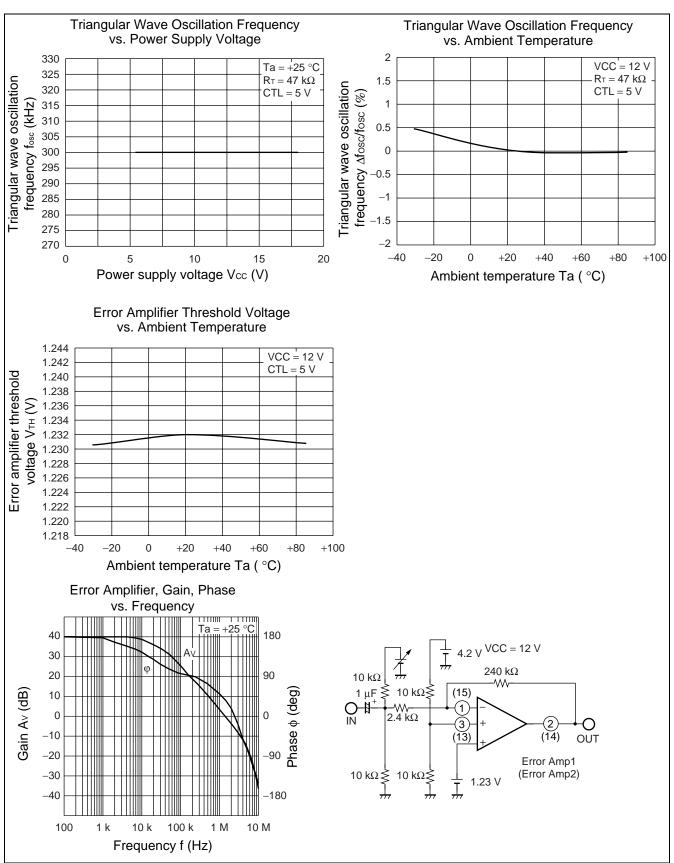
 $(VCC = 12 \text{ V}, VB = 0 \text{ mA}, VREF = 0 \text{ mA}, Ta = +25 ^{\circ}C)$

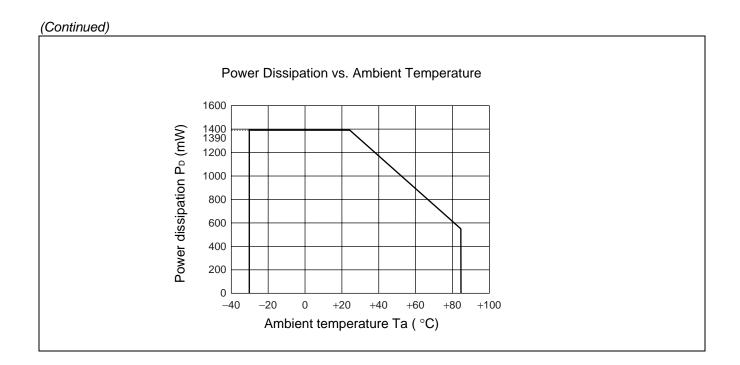
Para	motor	Symbol	Pin	Conditions		Value	,	Unit
Faia	Parameter		No.	Conditions	Min	Тур	Max	Oilit
	Output voltage (synchronous	V _{OH2}	19, 27	OUT2 = - 100 mA	3.5	5.1	_	V
	rectification side)	V _{OL2}	19, 27	OUT2 = 100 mA	_	1.0	1.4	V
Output Block	Diode voltage	VD	16, 30	VB = 10 mA	_	0.8	1.0	V
[Drive]	Dead time	t D1	29, 27, 17, 19	OUT1 = OUT2 = OPEN, VS = 0 V OUT2 :	40	80	120	ns
	Dead time	t D2	29, 27, 17, 19	OUT1 = OUT2 = OPEN, VS = 0 V OUT1 :	60	120	180	ns
	Output ON condition	Von	9, 10	_	2	_	VREF	>
	Output OFF condition	Voff	9, 10	_	0	_	0.8	>
Control Block [CTL, CTL1, CTL2]	Output ON condition	Von	6	_	2	_	Vcc	>
CTL2J	Output OFF condition	Voff	6	_	0	_	0.8	٧
	Input current	la-	9, 10	CTL1 = CTL2 = 0 V	- 44	- 35	- 29	μΑ
	input current	ICTL	6	CTL = 5 V	_	50	75	μΑ
General	Standby current	Iccs	24	CTL = 0 V	_	0	10	μΑ
General	Power-supply current	Icc	24	CTL = 5 V	_	15	23	mA

^{*:} Standard design value

■ TYPICAL CHARACTERISTICS







■ FUNCTIONS

1. DC/DC Converter Functions

(1) Reference voltage block (Ref)

The reference voltage circuit generates a temperature-compensated reference voltage (typically 3.5 V) using the voltage supplied from the power supply terminal (pin 24) . The voltage is used as the reference voltage for the IC's internal circuit.

The reference voltage can be used to supply a load current of up to 1 mA to an external device through the VREF terminal (pin 8).

(2) Triangular-wave oscillator block (OSC)

The triangular waveform oscillator incorporates a triangular oscillation frequency setting capacitor connected respectively to the RT terminal (pin 5) to generate triangular oscillation waveforms CT1 (amplitude of 1.8 V to 3.0 V) and CT2 (amplitude of 1.8 V to 3.0 V in antiphase with CT1). The symmetrical-phase system using the two opposite-phase triangular waves reduces the input ripple current, resulting in a smaller input capacitor.

The triangular oscillation waveforms are input to the IC's internal PWM comparator.

(3) Error amplifier block (Error Amp1, Error Amp2)

The error amplifier detects the DC/DC converter output voltage and outputs PWM control signals. By connecting a feedback resistor and capacitor between the output terminal and inverted input terminal, it is possible to create any desired level of loop gain, thereby providing stable phase compensation to the system.

Also, it is possible to prevent rush current at power supply start-up by connecting a soft-start capacitor to the CS1 terminal (pin 3) or CS2 terminal (pin 13), the non-inverted input terminal for Error Amp. The use of Error Amp for soft-start detection makes it possible for a system to operate on a fixed soft-start time that is independent of the output load on the DC/ DC converter.

(4) PWM comparator block (PWM Comp.)

The PWM comparator is a voltage-pulse width modulator that controls the output duty depending on the input/output voltage.

Main side: Turns the output transistor on in the intervals in which the error amplifier output voltage is higher than the triangular wave voltage.

Synchronous rectification side: Turns the output transistor on in the intervals in which the error amplifier output voltage is lower than the triangular wave voltage.

(5) Output block

The output circuits on the main side and on the synchronous rectification side are both in the totem pole configuration, capable of driving an external N-ch MOS FET.

In addition, because the output drive ability (700 mA Max : Duty $\leq 5\%$) is high, the gate – source capacity is large and the FET of low ON resistor can be used.

2. Channel Control Function

Channels, main, VB and PWRGOOD are turned on and off depending on the voltage levels at the CTL terminal (pin 6), CTL1 terminal (pin 9) and CTL2 terminal (pin 10).

CTL	CTL1	CTL2	Power	CH1	CH2	VB	PWRGOOD
L	*	*	OFF	OFF	OFF	OFF	OFF
Н	L	L	ON	OFF	OFF	ON	ON
Н	Н	L	ON	ON	OFF	ON	ON
Н	L	Н	ON	OFF	ON	ON	ON
Н	Н	Н	ON	ON	ON	ON	ON

^{*:} Undefined

3. Protective Functions

(1) Undervoltage lockout protection circuit (UVLO)

The transient state or a momentary drops in supply voltage, which occurs when the power supply is turned on, may cause the control IC to malfunction, resulting in breakdown or degradation of the system. To prevent such malfunctions, the undervoltage lockout protection circuit detects the internal reference voltage level with respect to the power supply voltage, turns off the output transistor, and sets the dead time to 100% while holding the CSCP terminal (pin 11) at the "L" level and setting the PWRGOOD terminal (pin 12) to the "L" level.

The system is restored when the supply voltage reaches the threshold voltage of the undervoltage lockout protection circuit.

(2) Timer-latch overcurrent protection circuit block (OCP)

The timer-latch overcurrent protection circuit is actuated upon completion of the soft-start period. When an overcurrent flows, the circuit detects the increase in the voltage between the main-side FET's drain and source using the main-side FET ON resistor, actuates the timer circuit, and starts charging the capacitor C_{SCP} connected to the CSCP terminal (pin 11). If the overcurrent remains flowing beyond the predetermined period of time, the circuit sets the latch to turn off the FETs on the main side and synchronous rectification side of each channel while setting the PWRGOOD terminal (pin 12) to the "L" level. The detection current value can be set by resistor RLIM1 connected between the main-side FET's drain and the ILIM1 terminal (pin 25) and resistor RLIM2 connected between the drain and the ILIM2 terminal (pin 23).

To reset the actuated protection circuit, either the power supply turn off and on again or set the CTL terminal (pin 6) to the "L" level to lower the VREF terminal (pin 8) voltage to 1.7 V (Min) or less. It can also be reset by setting both of the CTL1 terminal (pin 9) and CTL2 terminal (pin 10) to the "L" level. (Refer to "1. Setting Timer-Latch Overcurrent Detection Current" in ■ ABOUT TIMER-LATCH PROTECTION CIRCUIT.)

(3) Timer-latch short-circuit protection circuit (SCP)

The short-circuit detection comparator (SCP Comp.) detects the output voltage level and, if the error amplifier output voltage of either channel reaches the short-circuit detection voltage (typically 3.1 V), the timer circuit is actuated to start charging the external capacitor Cscp connected to the CSCP terminal (pin 11).

When the capacitor voltage reaches about 0.7 V, the circuit turns off the output transistor and sets the dead time to 100%.

The PWRGOOD terminal (pin 12) is fixed at the "L" level.

To reset the actuated protection circuit, either the power supply turn off and on again or set the CTL terminal (pin 6) to the "L" level to lower the VREF terminal (pin 8) voltage to 1.7 V (Min) or less. It can also be reset by setting both of the CTL1 terminal (pin 9) and CTL2 terminal (pin 10) to the "L" level. (Refer to "2. Setting Time Constant for Timer-Latch Short-Circuit Protection Circuit" in ■ ABOUT TIMER-LATCH PROTECTION CIRCUIT.)

(4) Timer-latch overvoltage protection circuit block (OVP)

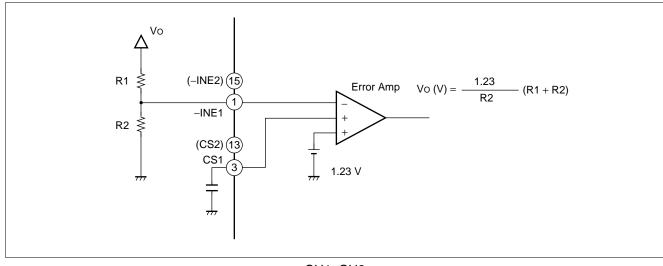
When the overvoltage detection comparator (OVP Comp.) provided for each channel detects the DC/DC converter's output voltage level exceeding its threshold voltage, the timer-latch overvoltage protection circuit actuates the timer circuit and starts charging the capacitor C_{SCP} connected to the CSCP terminal (pin 11). If the overvoltage remains applied beyond the predetermined period of time, the circuit sets the latch to turn off the FET on the main side of each channel while setting the PWRGOOD terminal (pin 12) to the "L" level.

To reset the actuated protection circuit, either the power supply turn off and on again or set the CTL terminal (pin 6) to the "L" level to lower the VREF terminal (pin 8) voltage to 1.7 V (Min) or less. It can also be reset by setting both of the CTL1 terminal (pin 9) and CTL2 terminal (pin 10) to the "L" level. (Refer to "3. Setting Overvoltage Detection by the Timer-Latch Overvoltage Protection Circuit" in ■ ABOUT TIMER-LATCH PROTECTION CIRCUIT.)

(5) Protection status output circuit block (PWRGOOD)

The protection status output circuit outputs the "L" level signal to the PWRGOOD terminal (pin 12) when each protection circuit is actuated.

■ SETTING THE OUTPUT VOLTAGE



< CH1, CH2 >

■ SETTING THE TRIANGULAR OSCILLATION FREQUENCY

The triangular oscillation frequency is determined by the timing resistor (R_T) connected to the RT terminal (pin 5). Triangular oscillation frequency: fosc

■ SETTING THE SOFT-START AND DISCHARGE TIMES

To prevent rush currents when the IC is turned on, you can set a soft-start by connecting soft-start capacitors (Cs1 and Cs2) to the CS1 terminal (pin 3) for channel 1 and the CS2 terminal (pin 13) for channel 2, respectively.

Setting the each control terminals (CTL1 and CTL2) from "L" to "OPEN" switches SW1 and SW2 from B to A to charge the external soft-start capacitors (C_{S1} and C_{S2}) connected to the CS1 and CS2 terminals at 3 μ A.

The error amplifier output (FB1 or FB2) is determined by comparison between the lower one of the potentials at two noninverted input terminals (1.23 V, CS terminal voltages) and the inverted input terminal voltage (-INE).

The FB terminal voltage during the soft-start period is therefore determined by comparison between the -INE terminal and CS terminal voltages. The DC/DC converter output voltage rises in proportion to the CS terminal voltage as the soft-start capacitor connected to the CS terminal is charged.

The soft-start time is obtained from the following equation:

Soft-start time: ts (time to output 100%)

ts (s)
$$\Rightarrow$$
 0.41 \times Cs (μ F)

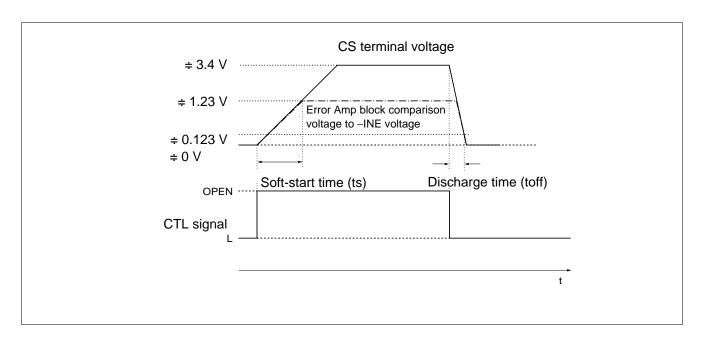
Setting the each control terminals (CTL1 and CTL2) from "OPEN" to "L" switches SW1 and SW2 from A to B.

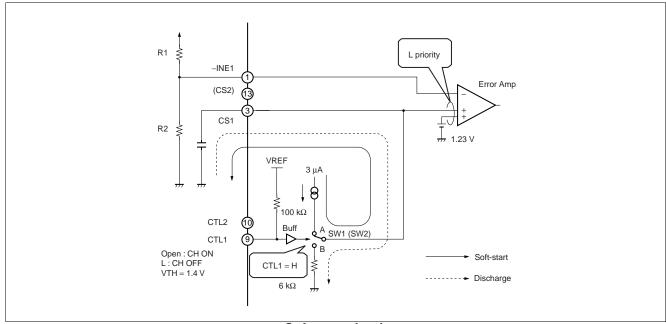
Then the IC discharges the soft-start capacitors (C_{S1} and C_{S2}) charged at about 3.4 V using the internally set discharge resistor ($Rs \neq 6 \text{ k}\Omega$) and lowers the output voltage regardless of the DC/DC converter load current.

The discharge time is obtained from the following equation:

Discharge time: toff (time to output 10%)

toff (s)
$$\neq$$
 0.020 \times Cs (μ F)

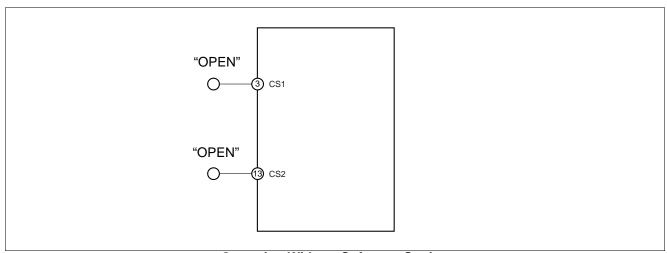




<Soft-start circuit>

■ TREATMENT OF UNUSED CS TERMINALS

When the soft-start function is not used, the CS1 terminal (pin 3) and CS2 terminal (pin 13) should be left open.



< Operation Without Soft-start Setting >

■ ABOUT TIMER-LATCH PROTECTION CIRCUIT

1. Setting Timer-Latch Overcurrent Detection Current

The overcurrent protection circuit is actuated upon completion of the soft-start period. When an overcurrent flows, the circuit detects the increase in the voltage between the main-side FET's drain and source using the main-side FET ON resistor (Ron), actuates the timer circuit, and starts charging the capacitor Cscp connected to the CSCP terminal (pin 11). If the overcurrent remains flowing beyond the predetermined period of time, the circuit sets the latch to turn off the FETs on the main side and synchronous rectification side of each channel while setting the PWRGOOD terminal (pin 12) to the "L" level. The detection current value can be set by the resistors (RLIM1 and RLIM2) connected between the main-side FET's drain and the ILIM1 terminal (pin 25) and between the drain and the ILIM2 terminal (pin 23), respectively.

The internal current (ILIM) can be set by the timing resistor (R₁) connected to the RT terminal (pin 5).

Internal current value: ILIM

$$I_{\text{LIM}}(\mu A)
ightharpoons = \frac{5546}{R_{\text{T}}(k\Omega)}$$

Detection current value: IOCP

$$\mathsf{locp} \; (\mathsf{A}) \; \doteq \; \frac{ \; \mathsf{ILIM}(\mathsf{A}) \times \mathsf{RLIM}(\Omega) \;}{\mathsf{Ron} \; (\Omega)} \; - \; \frac{ \; (\mathsf{V}_\mathsf{IN}(\mathsf{V}) - \mathsf{Vo}(\mathsf{V})) \times \mathsf{Vo}(\mathsf{V}) \;}{2 \times \mathsf{V}_\mathsf{IN}(\mathsf{V}) \times \mathsf{fosc}(\mathsf{Hz}) \times \mathsf{L}(\mathsf{H})}$$

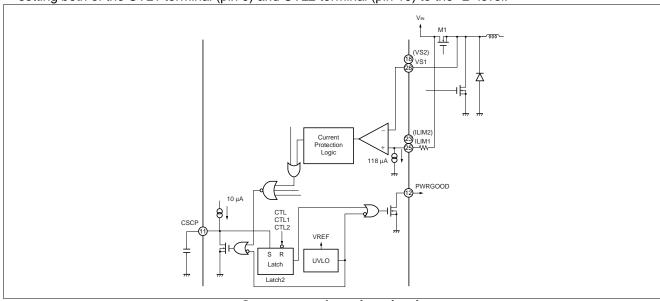
R_{LIM}: Overcurrent detection resistor R_{ON}: Main-side FET ON resistor

VIN: Input voltage

Vo: DC/DC converter output voltage

fosc: Oscillation frequency

L: Coil inductance



<Overcurrent detection circuit>

2. Setting Time Constant for Timer-Latch Short-Circuit Protection Circuit

Each channel uses the short-circuit detection comparator (SCP Comp.) to always compare the error amplifier's output level to the reference voltage.

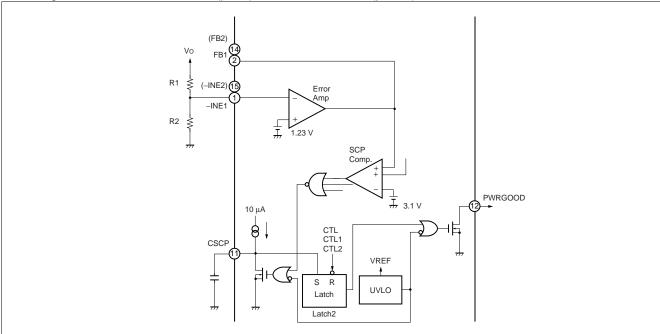
While the DC/DC converter load conditions are stable on both channels, the short-circuit detection comparator keeps its output at the "H" level and the CSCP terminal (pin 11) remains at the "L" level.

If a load condition changes rapidly due to a short-circuit of the load, causing the output voltage to drop, the short-circuit detection comparator changes its output to the "L" level. This causes the external short-circuit protection capacitor Cscp connected to the CSCP terminal to be charged at 10 µA.

Short-circuit detection time (tscp)

$$t_{SCP}(s) = 0.070 \times C_{SCP}(\mu F)$$

When capacitor Cscp is charged to the threshold voltage (V_{TH} ≠ 0.70 V), the protection circuit sets the latch and turns off the external FET (setting the dead time to 100%). At this time, the latch input is closed. As the result, the CSCP terminal is held at the "L" level and the PWRGOOD terminal is set to "L" level. The protection circuit closes both channels even when a short-circuit is detected on only either.



<Timer-latch short-circuit protection circuit>

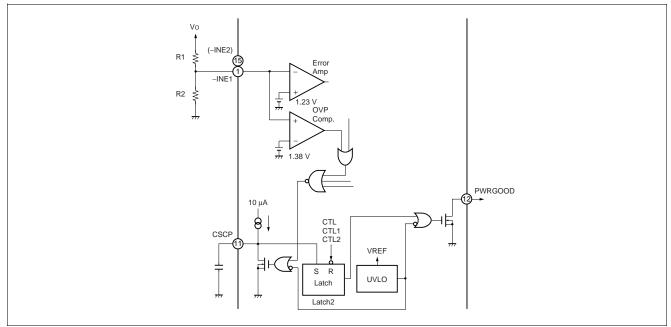
3. Setting Overvoltage Detection by the Timer-Latch Overvoltage Protection Circuit

An overvoltage output from the DC/DC converter can be detected by connecting external resistors from the DC/DC converter output to the noninverted input terminal (-INE1 terminal (pin 1) and -INE2 terminal (pin 15)) of the overvoltage comparators (OVP Comp. 1 and OVP Comp. 2).

When the DC/DC converter output voltage exceeds the overvoltage detection level, the output of the overvoltage comparator (OVP Comp. 1 and OVP Comp. 2) becomes the "H" level and the overvoltage protection circuit actuates the timer circuit to start charging the external capacitor Cscp connected to the CSCP terminal (pin 11). If the overvoltage remains applied beyond setting time, the circuit sets the latch to turn off the FET on the main side of each channel while setting the PWRGOOD terminal (pin 12) to the "L" level. The protection circuit closes both channels even when an overvoltage is detected on only either.

Overvoltage detection voltage: Vove

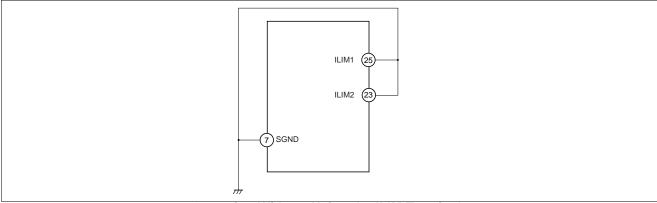
Vovp (V)
$$\Rightarrow$$
 1.38 \times (R1 (Ω) + R2 (Ω)) / R2 (Ω) \Rightarrow 1.12 \times Vo



<Timer-latch overvoltage protection circuit>

■ TREATMENT OF UNUSED ILIM TERMINALS

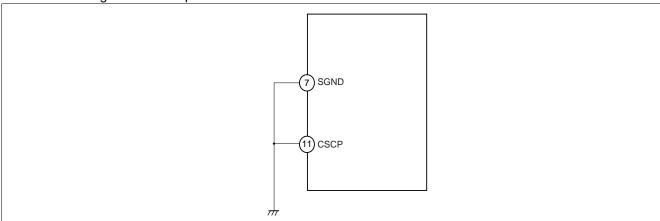
When the overcurrent protection circuit is not used, the ILIM1 terminal (pin 25) and ILIM2 terminal (pin 23) should be shorted to the SGND terminal.



<Operation Without Using the ILIM Terminals>

■ PROCESSING WITHOUT USING THE CSCP TERMINAL

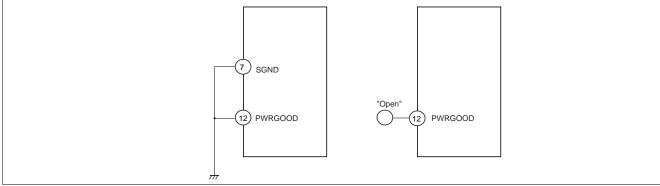
When the timer-latch short-circuit protection circuit is not used, the CSCP terminal (pin 11) should be shorted to SGND using the shortest possible connection.



<Operation Without Using the CSCP Terminal>

■ TREATMENT OF UNUSED PWRGOOD TERMINALS

When the PWRGOOD terminal is not used, the PWRGOOD terminal (pin 12) should be shorted or open to the SGND terminal.



<Operation Without Using the PWRGOOD Terminals>

■ OUTPUT STATES DURING PROTECTION CIRCUIT OPERATION

The table below lists the output states with each protection circuit actuated.

Out	CI	H1	CH2		PWRGOOD	
Protection circuit		OUT1-1	OUT2-1	OUT1-2	OUT2-2	PWKGOOD
Overcurrent protection circuit	CH1	L	L	L	L	L
Overcurrent protection circuit	CH2	L	L	L	L	L
Overvoltage protection circuit	CH1	L	Н	L	Н	L
Overvoitage protection circuit	CH2	L	Н	L	Н	L
Short-circuit protection	CH1	L	L	L	L	L
Short-circuit protection	CH2	L	L	L	L	L
Under voltage lockout protection	on circuit	L	L	L	L	L

■ RESETTING THE LATCH OF EACH PROTECTION CIRCUIT

When the overvoltage, overcurrent, or short-circuit protection circuit detects each abnormality, it sets the latch to fix the output at the "L" level. The PWRGOOD terminal (pin 12) is fixed at the "L" level upon abnormality detection by each protection circuit.

■ NOTE ON IC'S INTERNAL POWER CONSUMPTION

The oscillation frequency of an IC and the total gate charge of FETs largely affects the internal dissipation of the IC.

Pay attention to the following point with respect to the internal power consumption of the IC when applications are used.

I_B (mean current) is obtained from the following equation, assuming Qg1 and Qg2 as the total gate charges applied to the gate capacitors (Ciss₁, Ciss₂, Crss₁, Crss₂) of external FETs Q1 and Q2.

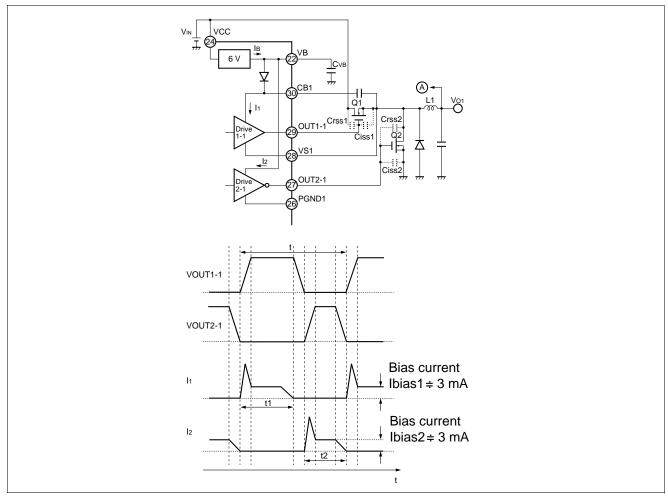
Current per channel

$$\begin{array}{lll} I_{B}\left(A\right) & = & I_{1}+I_{2} \\ & \Rightarrow & Ibias1 \times \frac{t1}{t} + \frac{Qg_{1}}{t} + & Ibias2 \times \frac{t2}{t} + \frac{Qg_{2}}{t} \left(Ibias1 = Ibias2 \div 3 \text{ mA}\right) \end{array}$$

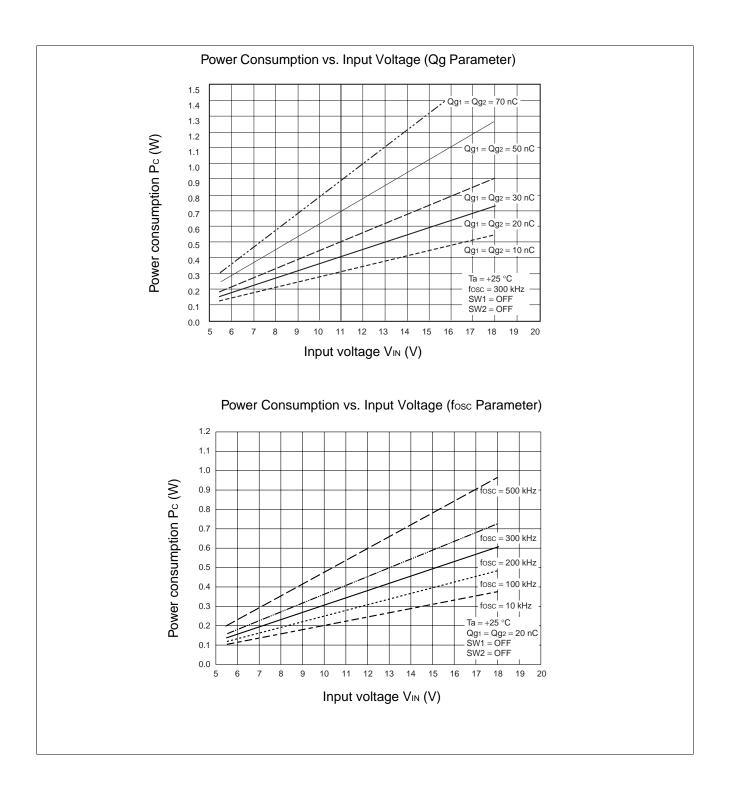
As the current consumption by the IC, excluding I_B, is about 15 mA, the power consumption is obtained from the following equation :

Power consumption : Pc

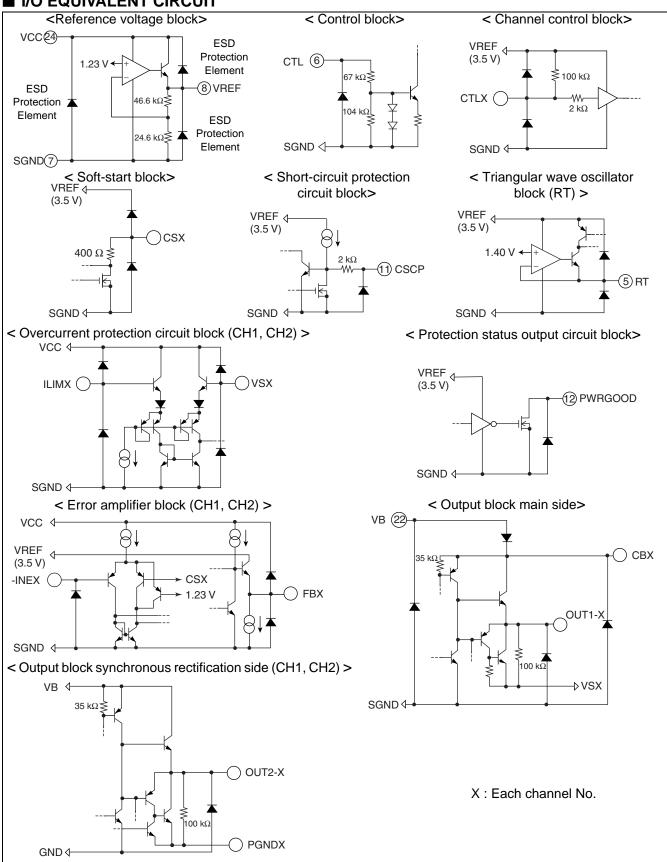
$$Pc (W) = 0.015 \times Vcc (V) + 2 \times Vcc (V) \bullet I_B (A) - V_B (V) \bullet I_B (A)$$



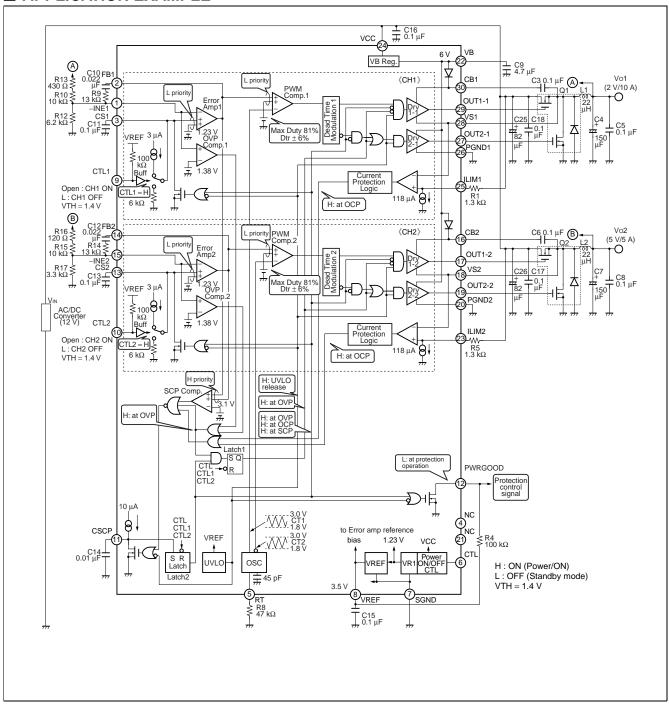
Refer to "Power Consumption vs. Input Voltage" on the next page as a reference and use the above method of obtaining the power consumption to design your application of the IC taking account of the "Power Dissipation vs. Ambient Temperature" characteristic in the ■ TYPICAL CHARACTERISTICS.



■ I/O EQUIVALENT CIRCUIT



■ APPLICATION EXAMPLE



■ PARTS LIST

COMPONENT	ITEM	SPECI	FICATION	VENDOR	PARTS NO.
Q1, Q2	Dual FETKY™	Main sides: VDS = 30 V, Qg = 9.9 nC (Max) Synchronous sides: VDS = 30 V, Qg = 20.7 nC (Max) SBD: $VF = 0.52 \text{ V (Max)}$ at $IF = 1 \text{ A}$		IR	IRF7901D1
L1, L2	Coil	22 μΗ	$3.5~\text{A},31.6~\text{m}\Omega$	TDK	SLF12565T- 220M3R5
C3, C6	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C4	OS-CON™	150 μF	6.3 V	SANYO	6SVP150M
C5, C8	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C7	OS-CON™	150 μF	6.3 V	SANYO	6SVP150M
C9	Ceramics Condenser	4.7 μF	10 V	TDK	C3216JB1A475M
C10	Ceramics Condenser	0.022 μF	50 V	TDK	C1608JB1H223K
C11, C13	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C12	Ceramics Condenser	0.022 μF	50 V	TDK	C1608JB1H223K
C14	Ceramics Condenser	0.01 μF	50 V	TDK	C1608JB1H103K
C15, C16	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C17, C18	Ceramics Condenser	0.1 μF	50 V	TDK	C1608JB1H104K
C25, C26	OS-CON™	82 μF	16 V	SANYO	16SVP82M
R1, R5	Resistor	1.3 Ω	0.5 %	ssm	RR0816P132D
R4	Resistor	100 kΩ	0.5 %	ssm	RR0816P104D
R8	Resistor	47 kΩ	0.5 %	ssm	RR0816P473D
R9	Resistor	13 kΩ	0.5 %	ssm	RR0816P133D
R10	Resistor	10 kΩ	0.5 %	ssm	RR0816P103D
R12	Resistor	6.2 kΩ	0.5 %	ssm	RR0816P622D
R13	Resistor	430 Ω	0.5 %	ssm	RR0816P434D
R14	Resistor	13 kΩ	0.5 %	ssm	RR0816P133D
R15	Resistor	10 kΩ	0.5 %	ssm	RR0816P103D
R16	Resistor	120 Ω	0.5 %	ssm	RR0816P124D
R17	Resistor	3.3 kΩ	0.5 %	ssm	RR0816P332D

Note: IR: International Rectifier Corp.

TDK: TDK Corporation

SANYO: SANYO Electric Co., Ltd. ssm: SUSUMU Electronics Corp.

Dual FETKY is a trademark of International Rectifier Corp.

OS-CON is a trademark of SANYO Electric Co., Ltd.

■ SELECTION OF COMPONENTS

• N-ch MOS FET

The N-ch MOS FET for switching use should be rated for at least 20% more than the maximum input voltage. To minimize continuity loss, use a FET with low R_{DS(ON)} between the drain and source. For high input voltage and high frequency operation, on/off-cycle switching loss will be higher so that power dissipation must be considered. In this application, the IR IRF7901D1 is used. Continuity loss, on/off switching loss, and total loss are determined by the following formulas. The selection must ensure that peak drain current does not exceed rated values, and also must be in accordance with overcurrent detection levels.

Continuity loss :
$$P_C$$

 $P_C = I_D^2 \times R_{DS}$ (on) \times Duty

On-cycle switching loss : Ps (on)

$$P_{S}(on) = \frac{V_{D}(Max) \times I_{D} \times tr \times fosc}{6}$$

$$\begin{array}{l} \text{Off-cycle switching loss: Ps (off)} \\ \text{Ps (off)} = \frac{\text{Vp (Max)} \times \text{Ip (Max)} \times \text{tf} \times \text{fosc}}{6} \end{array}$$

$$P_T = P_C + P_S \text{ (ON)} + P_S \text{ (OFF)}$$

Example: Using the IR IRF7901D1

CH1 Main side

Input voltage V_{IN} (Max) = 15 V, output voltage V_0 = 3.3 V, drain current I_D = 3 A, Oscillation frequency fosc = 300 kHz, L = 22 μ H, drain-source on resistance R_{DS} (on) \div 33 m Ω , tr = 13.8 ns, tf = 8 ns.

Drain current (Max) : I_D (Max)
I_D (Max) = I_O +
$$\frac{V_{IN} (Max) - V_{O}}{2L}$$
 ton
= 3 + $\frac{15 - 3.3}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.22$
 $\Rightarrow 3.20 (A)$

Drain current (Min) : I_D (Min)
I_D (Min) = I_O
$$-\frac{V_{IN} (Max) - V_{O}}{2L}$$
 ton
= $3 - \frac{15 - 3.3}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.22$
 $\Rightarrow 2.80 (A)$

Pc1 =
$$I_D^2 \times R_{DS}$$
 (on) × Duty (on)
= $3^2 \times 0.033 \times 0.22$
÷ 0.065 W

$$\begin{array}{ll} \mathsf{Ps1} \; \mathsf{(ON)} & = \; \frac{\mathsf{V_D} \; \mathsf{(Max)} \; \times \mathsf{I_D} \times \mathsf{tr} \times \mathsf{fosc}}{6} \\ \\ & = \; \frac{15 \times 3 \times 13.8 \times 10^{-9} \times 300 \times 10^3}{6} \end{array}$$

≑ <u>0.031 W</u>

$$Ps_1 (OFF) = \frac{V_D (Max) \times I_D (Max) \times tf \times fosc}{6}$$

$$= \frac{15 \times 3.2 \times 8 \times 10^{-9} \times 300 \times 10^3}{6}$$

$$= \frac{0.019 W}{6}$$

$$P_{T1} = P_{C1} + P_{S1} (o_N) + P_{S1} (o_{FF})$$

 $\div 0.065 + 0.031 + 0.019$
 $\div 0.115 W$

CH1 (Synchronous rectification side)

Input voltage V_{IN} (Max) = 15 V, output voltage $V_O = 3.3$ V, drain current $I_D = 3$ A, oscillation frequency fosc = 300 kHz, L = 22 μ H, drain-source on resistance R_{DS} (on) \doteqdot 28 m Ω , tr = 16.4 ns, tf = 5.2 ns.

I_D (Max) = I_O +
$$\frac{V_O}{2L}$$
 toff
= 3 + $\frac{3.3}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^3} \times (1-0.22)$
 $\Rightarrow 3.20$ (A)

Drain current (Min): ID (Min)

I_D (Min) = I_O
$$-\frac{V_O}{2L}$$
 toff
= 3 $-\frac{3.3}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^3} \times (1-0.22)$
 $=\frac{2.80 \text{ (A)}}{2}$

$$\begin{array}{lll} P_{C2} &=& I_{D^2} \times R_{DS} \, (\text{on}) \, \times \text{Duty} \, (\text{opf}) \\ &=& 3^2 \times 0.028 \times \, (1-0.22) \\ & \doteq & 0.197 \, W \\ \\ P_{S2} \, (\text{on}) &=& \frac{V_D \, (\text{Max}) \, \times I_D \times \text{tr} \times \text{fosc}}{6} \\ &=& \frac{15 \times 3 \times 16.4 \times 10^{-9} \times 300 \times 10^3}{6} \\ & \doteq & 0.037 \, W \\ \\ P_{S2} \, (\text{off}) &=& \frac{V_D \, (\text{Max}) \, \times I_D \, (\text{Max}) \, \times \text{tf} \times \text{fosc}}{6} \\ &=& \frac{15 \times 3.2 \times 5.2 \times 10^{-9} \times 300 \times 10^3}{6} \\ & \doteq & 0.012 \, W \\ \\ P_{T2} &=& P_{C2} + P_{S2} \, (\text{on}) \, + P_{S2} \, (\text{off}) \\ & \doteq & 0.197 + 0.037 + 0.012 \\ & \doteq & 0.246 \, W \\ \\ P_{T} &=& P_{T1} + P_{T2} \\ & \doteq & 0.115 + 0.246 \\ & \doteq & 0.361 \, W \\ \end{array}$$

The above power dissipation figures for the IRF7901D1 are satisfied with ample margin at 2W ($Ta = +100 \, ^{\circ}C$).

CH2 (Main side)

Input voltage V_{IN} (Max) = 15 V, output voltage $V_0 = 5$ V, drain current $I_D = 3$ A, Oscillation frequency fosc = 300 kHz, $L = 22 \mu H$, drain-source on resistance R_{DS} (ON) \doteqdot 33 m Ω , tr = 13.8 ns, tf = 8 ns.

Drain current (Max) : I_D (Max)
I_D (Max) = I_O +
$$\frac{V_{IN} (Max) - V_{O}}{2L}$$
 ton
= 3 + $\frac{15-5}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.33$
 $\Rightarrow 3.25 (A)$

$$I_{D} (Min) = I_{O} + \frac{V_{IN} (Max) - V_{O}}{2L} ton$$

$$= 3 - \frac{15 - 5}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.33$$

$$\stackrel{\div}{=} 2.75 (A)$$

$$\begin{array}{lll} P_{C1} & = & I_{D^2} \times R_{DS} \text{ (on)} \times Duty \text{ (on)} \\ & = & 3^2 \times 0.033 \times 0.33 \\ & & \div & 0.098 \text{ W} \end{array}$$

Ps1 (ON) =
$$\frac{V_D (Max) \times I_D \times tr \times fosc}{6}$$

= $\frac{15 \times 3 \times 13.8 \times 10^{-9} \times 300 \times 10^3}{6}$
 $\Rightarrow 0.031 \text{ W}$

$$P_{\text{S1 (OFF)}} = \frac{V_{\text{D (Max})} \times I_{\text{D (Max})} \times tf \times fosc}{6}$$

$$= \frac{15 \times 3.25 \times 8 \times 10^{-9} \times 300 \times 10^{3}}{6}$$

$$P_{T1} = P_{C1} + P_{S1} (o_N) + P_{S1} (o_{FF})$$

 $\div 0.098 + 0.031 + 0.020$
 $\div 0.149 W$

CH2 (Synchronous rectification side)

Input voltage V_{IN} (Max) = 15 V, output voltage $V_0 = 5$ V, drain current $I_D = 3$ A, Oscillation frequency fosc = 300 kHz, L = 22 μ H, drain-source on resistance R_{DS} (ON) \doteqdot 28 m Ω , tr = 16.4 ns, tf = 5.2 ns.

Drain current (Max) : I_D (Max)
$$I_{D} (Max) = I_{O} + \frac{V_{O}}{2L} \text{ toff}$$

$$= 3 + \frac{5}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times (1-0.33)$$

$$\stackrel{\div}{=} 3.25 (A)$$

$$I_D (Min) = I_O - \frac{V_O}{2L} \text{ toff}$$

= $3 - \frac{5}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^3} \times (1-0.33)$

$$P_{C2} = I_D^2 \times R_{DS} \text{ (oN)} \times Duty \text{ (OFF)}$$

= $3^2 \times 0.028 \times (1-0.33)$
\(\ddot\) 0.169 W

$$P_{S2} \text{ (ON)} = \frac{V_D \text{ (Max)} \times I_D \times tr \times fosc}{6}$$
$$= \frac{15 \times 3 \times 16.4 \times 10^{-9} \times 300 \times 10^{3}}{6}$$

$$P_{S2} \text{ (OFF)} = \frac{V_D \text{ (Max)} \times I_D \text{ (Max)} \times \text{tf} \times \text{fosc}}{6}$$

$$= \frac{15 \times 3.25 \times 5.2 \times 10^{-9} \times 300 \times 10^3}{6}$$

$$P_{T2} = P_{C2} + P_{S2} (o_N) + P_{S2} (o_{FF})$$

 $\Rightarrow 0.169 + 0.037 + 0.013$
 $\Rightarrow 0.219 \text{ W}$

$$P_T = P_{T1} + P_{T2} \text{ (OFF)}$$

 $\Rightarrow 0.149 + 0.219$
 $\Rightarrow 0.368 \text{ W}$

The above power dissipation figures for the IRF7901D1 are satisfied with ample margin at 2W ($Ta = +100 \, ^{\circ}C$).

• Inductors

In selecting inductors, it is of course essential not to apply more current than the rated capacity of the inductor, but also to note that the lower limit for ripple current is a critical point that if reached will cause discontinuous operation and a considerable drop in efficiency. This can be prevented by choosing a higher inductance value, which will enable continuous operation under light loads. Note that if the inductance value is too high, however, direct current resistance (DCR) is increased and this will also reduce efficiency. The inductance must be set at the point where efficiency is greatest.

Note also that the DC superimposition characteristics become worse as the load current value approaches the rated current value of the inductor, so that the inductance value is reduced and ripple current increases, causing loss of efficiency. The selection of rated current value and inductance value will vary depending on where the point of peak efficiency lies with respect to load current.

Inductance values are determined by the following formulas.

The L value for all load current condition is set so that the peak to peak value of the ripple current is 1/2 the load current or less.

Inductance value : L
$$L \ge \frac{2 (V_{IN} - V_O)}{I_O} \text{ ton }$$

Example:

CH1
$$L \ge \frac{2 (V_{IN} (Max) - V_O)}{I_O} \text{ ton}$$

$$\ge \frac{2 \times (15 - 3.3)}{3} \times \frac{1}{300 \times 10^3} \times 0.22$$

$$\ge \underline{5.7 \, \mu H}$$

CH2
$$L \geq \frac{2 (V_{IN} (_{Max}) - V_{O})}{I_{O}} \text{ ton}$$

$$\geq \frac{2 \times (15 - 5)}{3} \times \frac{1}{300 \times 10^{3}} \times 0.33$$

$$\geq 7.3 \, \mu H$$

Inductance values derived from the above formulas are values that provide sufficient margin for continuous operation at maximum load current, but at which continuous operation is not possible at light loads. It is therefore necessary to determine the load level at which continuous operation becomes possible. In this application, the TDK SLF12565T-220M3R5 is used. At 22 μ H, the load current value under continuous operating conditions is determined by the following formula.

Load current value under continuous operating conditions : lo

$$I_0 \ge \frac{V_0}{2L}$$
 toff

Example : Using the SLF12565T-220M3R5 22 μ H (allowable tolerance $\pm 20\%$) , rated current = 3.5 A

CH1
Io
$$\geq \frac{V_0}{2L}$$
 toff
$$\geq \frac{3.3}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^3} \times (1-0.22)$$

$$\geq \underline{195 \text{ mA}}$$

CH2
$$I_{0} \geq \frac{V_{0}}{2L} \text{ toff}$$

$$\geq \frac{5}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times (1-0.33)$$

$$\geq 254 \text{ mA}$$

To determine whether the current through the inductor is within rated values, it is necessary to determine the peak value of the ripple current as well as the peak-to-peak values of the ripple current that affect the output ripple voltage. The peak value and peak-to-peak value of the ripple current can be determined by the following formulas.

Peak value : I
$$_L$$
 I $_L \ge I_O + \frac{V_{IN} - V_O}{2L}$ ton

Peak-to-peak value :
$$\Delta I_L$$

 $\Delta I_L = \frac{V_{IN} - V_O}{I}$ ton

Example: Using the SLF12565T-220M3R5 22 μ H (allowable tolerance $\pm 20\%$), rated current = 3.5 A

Peak value

$$\begin{array}{lll} \text{IL} & \geq & \text{Io} & + \frac{\text{V}_{\text{IN}} \left(\text{Max} \right) - \text{V}_{\text{O}}}{2 \text{L}} & \text{ton} \\ \\ & \geq & 3 & + \frac{15 - 3.3}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.22 \\ \\ & \geq & \frac{3.20 \text{ A}}{} \end{array}$$

IL
$$\geq$$
 Io $+\frac{V_{IN} (Max) - V_{O}}{2L}$ ton
 \geq 3 $+\frac{15-5}{2 \times 22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.33$
 \geq 3.25 A

Peak-to-peak value:

CH1
$$\Delta I_{L} = \frac{V_{IN} (M_{in}) - V_{O}}{L} \text{ ton}$$

$$= \frac{15 - 3.3}{22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.22$$

$$\stackrel{?}{=} \frac{0.39 \text{ A}}{L}$$
CH2
$$\Delta I_{L} = \frac{V_{IN} (M_{ax}) - V_{O}}{L} \text{ ton}$$

$$= \frac{15 - 5}{22 \times 10^{-6}} \times \frac{1}{300 \times 10^{3}} \times 0.33$$

$$\stackrel{?}{=} 0.5 \text{ A}$$

Smoothing Capacitor

The smoothing capacitor is an indispensable element for reducing ripple voltage in output. In selecting a smoothing capacitor it is essential to consider equivalent series resistance (ESR) and allowable ripple current. Higher ESR means higher ripple voltage, so that to reduce ripple voltage it is necessary to select a capacitor with low ESR. However, the use of a capacitor with low ESR can have substantial effects on loop phase characteristics, and therefore requires attention to system stability. Care should also be taken to use a capacity with sufficient margin for allowable ripple current. This application uses the 6SVP150M (OS-CON™: SANYO). The ESR, capacitance value, and ripple current can be calculated from the following formulas.

Equivalent Series Resistance : ESR

$$ESR \leq \frac{\Delta Vo}{\Delta I_L} - \frac{1}{2\pi f C_L}$$

Capacitance value : CL

$$C_{L} \geq \frac{\Delta I_{L}}{2\pi f \left(\Delta V_{O} - \Delta I_{L} \times ESR\right)}$$

Ripple current: ICLrms

$$IC_{Lrms} \ge \frac{(V_{IN} - V_O)}{2\sqrt{3}L}$$
 ton

Example: Using the 6SVP150M

Rated voltage = 6.3 V, ESR = 35 m Ω , maximum allowable ripple current = 2.35 Arms

Equivalent series resistance

CH1
ESR
$$\leq \frac{\Delta V_0}{\Delta I_L} - \frac{1}{2\pi f C_L}$$

 $\leq \frac{0.033}{0.39} - \frac{1}{2\pi \times 300 \times 10^3 \times 150 \times 10^{-6}}$
 $\leq 81.1 \text{ m}\Omega$

CH2
ESR
$$\leq \frac{\Delta V_0}{\Delta I_L} - \frac{1}{2\pi f C_L}$$

 $\leq \frac{0.05}{0.5} - \frac{1}{2\pi \times 300 \times 10^3 \times 150 \times 10^{-6}}$
 $\leq \frac{96.5 \text{ m}\Omega}{2\pi \times 300 \times 10^3 \times 150 \times 10^{-6}}$

Capacitance value

CH1

$$\begin{array}{l} C_{L} \geq \frac{\Delta I_{L}}{2\pi f \left(\Delta V_{0} - \Delta I_{L} \times ESR\right)} \\ \geq \frac{0.39}{2\pi \times 300 \times 10^{3} \times \left(0.033 - 0.39 \times 0.035\right)} \\ \geq 10.7 \ \mu F \end{array}$$

CH2

$$C_{L} \geq \frac{\Delta I_{L}}{2\pi f (\Delta V_{0} - \Delta I_{L} \times ESR)}$$

$$\geq \frac{0.5}{2\pi \times 300 \times 10^{3} \times (0.05 - 0.5 \times 0.035)}$$

$$\geq 8.2 \mu E$$

Ripple current

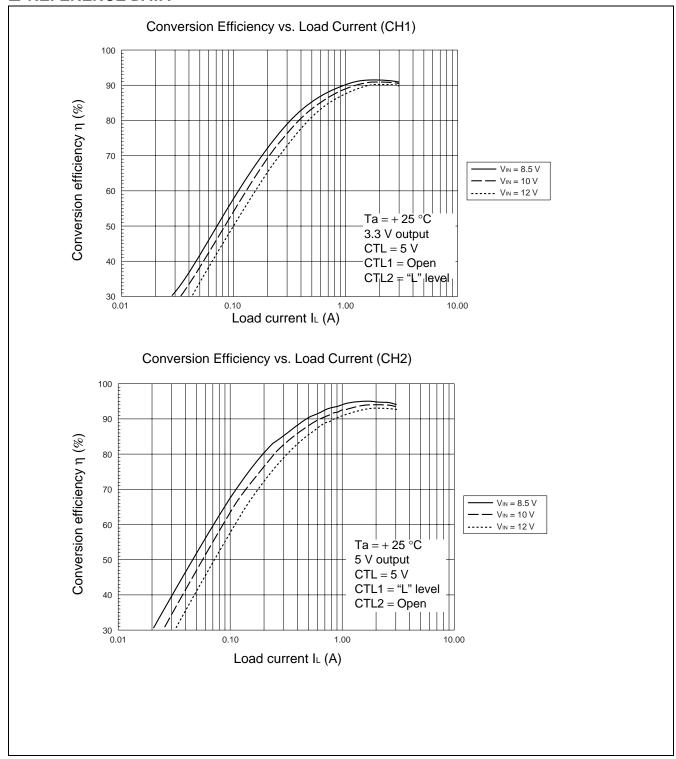
CH1

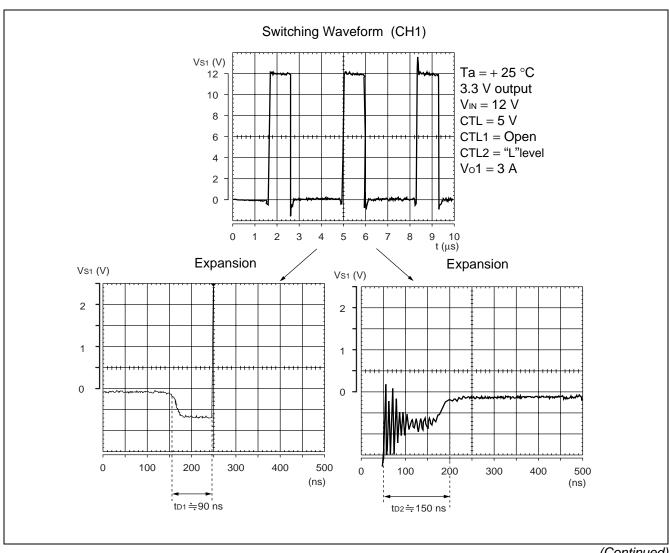
$$\begin{array}{ll} I_{\text{CLrms}} \; \geq \; \frac{\left(V_{\text{IN}} \left(_{\text{Max}} \right) \; - V_{\text{O}} \right)}{2 \sqrt{3} L} \; \; ton \\ \\ \geq \; \frac{\left(15 - 3.3 \right) \; \times 0.22}{2 \sqrt{3} L \times 22 \times 10^{-6} \times 300 \times 10^{3}} \\ \\ \geq \; \; 112.6 \; \text{mArms} \end{array}$$

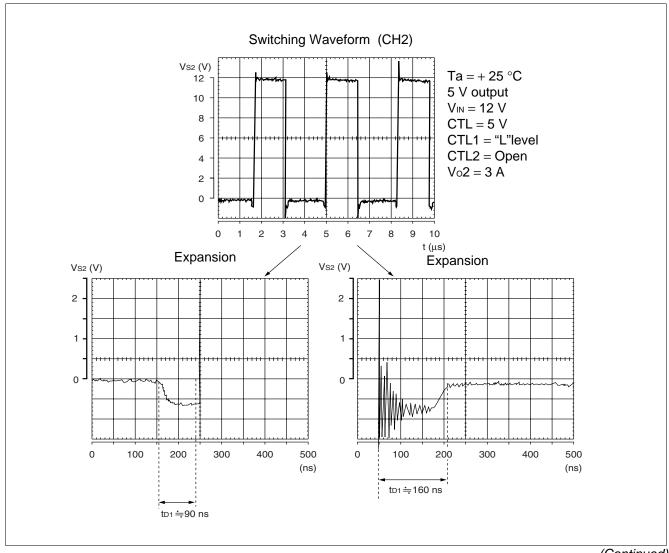
CH2

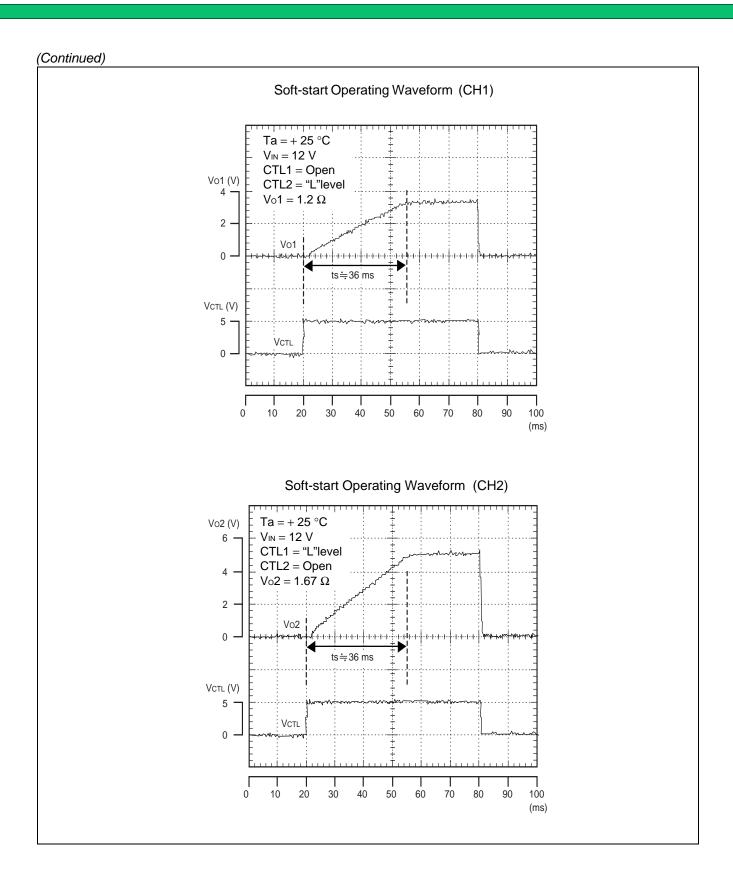
$$\begin{split} I_{\text{CLrms}} & \geq \frac{ \left(\text{V}_{\text{IN}} \left(\text{Max} \right) - \text{Vo} \right) \text{ton}}{2 \sqrt{3} L} \\ & \geq \frac{ \left(15 - 5 \right) \times 0.33}{2 \sqrt{3} L \times 22 \times 10^{-6} \times 300 \times 10^{3}} \\ & \geq \frac{114.3 \text{ mArms}}{2 \times 10^{-6} \times 300 \times 10^{3}} \end{split}$$

■ REFERENCE DATA









■ NOTES ON USE

- Take account of common impedance when designing the earth line on a printed wiring board.
- Take measures against static electricity.
 - For semiconductors, use antistatic or conductive containers.
 - When storing or carrying a printed circuit board after chip mounting, put it in a conductive bag or container.
 - The work table, tools, and measuring instruments must be grounded.
 - The worker must put on a grounding device containing 250 k Ω to 1 M Ω resistors in series.
- Do not apply a negative voltage.
 - Applying a negative voltage of -0.3 V or less to an LSI may generate a parasitic transistor, resulting in malfunction.

■ PRECAUTIONS ON HANDLING THIS PRODUCT

This product has obtained US patents for patent numbers of 6,147,477.

■ ORDERING INFORMATION

Part number	Package	Remarks
MB39A106PFT-□□□E1	30-pin plastic TSSOP (FPT-30P-M04)	Lead Free version

■ EV BOARD ORDERING INFORMATION

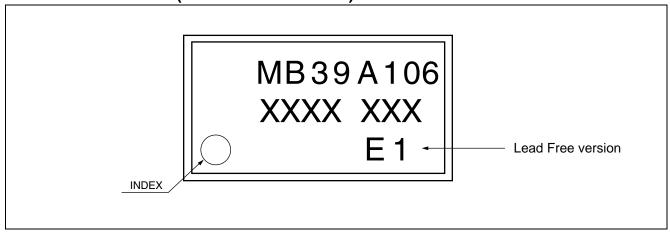
EV board part No.	EV board version No.	Remarks
MB39A106EVB	Board Rev. 2.0	TSSOP-30P

■ RoHS COMPLIANCE INFORMATION OF LEAD (Pb) FREE VERSION

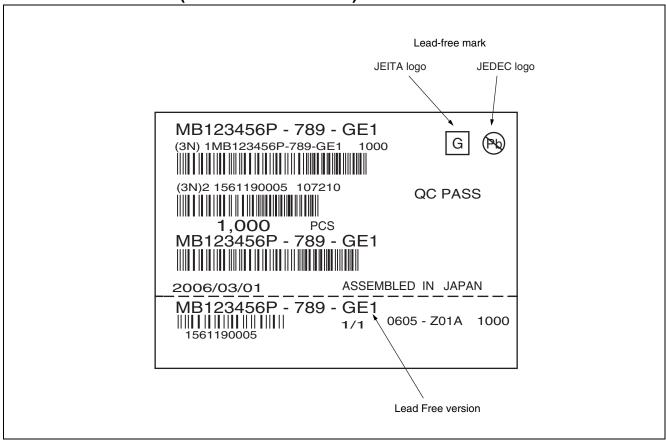
The LSI products of Fujitsu with "E1" are compliant with RoHS Directive, and has observed the standard of lead, cadmium, mercury, Hexavalent chromium, polybrominated biphenyls (PBB), and polybrominated diphenyl ethers (PBDE).

The product that conforms to this standard is added "E1" at the end of the part number.

■ MARKING FORMAT (LEAD FREE VERSION)



■ LABELING SAMPLE (LEAD FREE VERSION)

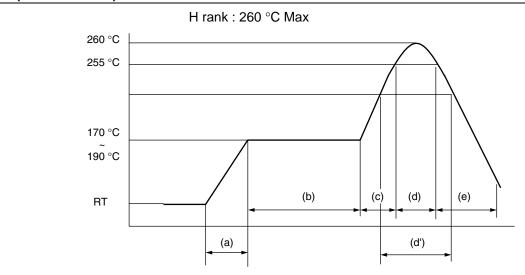


■ MB39A106PFT-□□□E1 RECOMMENDED CONDITIONS OF MOISTURE SENSITIVITY LEVEL

Item	Condition	
Mounting Method	IR (infrared reflow), Manual soldering (partial heating method)	
Mounting times	2 times	
Storage period	Before opening	Please use it within two years after Manufacture.
	From opening to the 2nd reflow	Less than 8 days
	When the storage period after opening was exceeded	Please processes within 8 days after baking (125 °C, 24H)
Storage conditions	5 °C to 30 °C, 70%RH or less (the lowest possible humidity)	

[Temperature Profile for FJ Standard IR Reflow]

(1) IR (infrared reflow)



(a) Temperature Increase gradient $\,$: Average 1 $^{\circ}\text{C/s}$ to 4 $^{\circ}\text{C/s}$

(b) Preliminary heating : Temperature 170 °C to 190 °C, 60 s to 180 s

(c) Temperature Increase gradient $\,$: Average 1 $^{\circ}\text{C/s}$ to 4 $^{\circ}\text{C/s}$

(d) Actual heating : Temperature 260 °C Max; 255 °C or more, 10 s or less

(d') : Temperature 230 °C or more, 40 s or less

or

Temperature 225 $^{\circ}\text{C}$ or more, 60 s or less

or

Temperature 220 °C or more, 80 s or less

(e) Cooling : Natural cooling or forced cooling

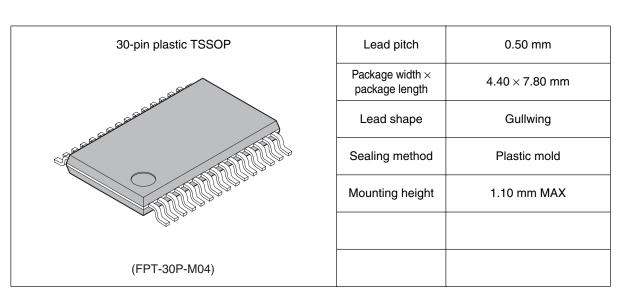
Note: Temperature: the top of the package body

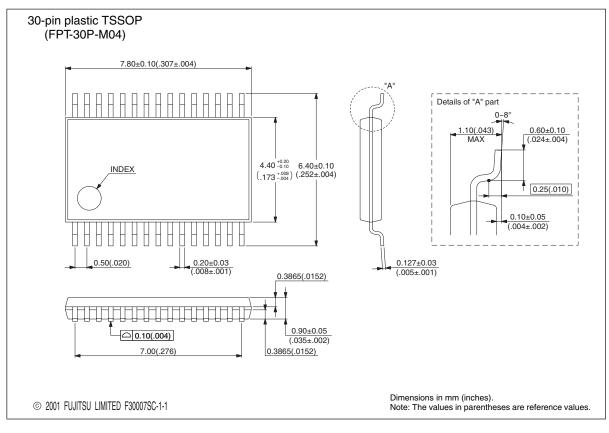
(2) Manual soldering (partial heating method)

Conditions: Temperature 400 °C Max

Times : 5 s max/pin

■ PACKAGE DIMENSION





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